Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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Contact us

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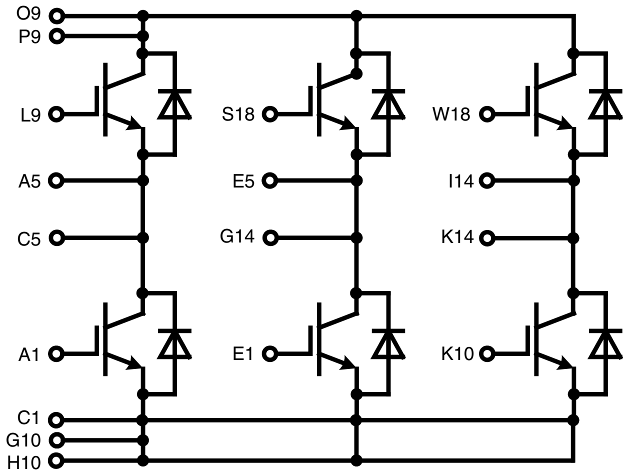
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

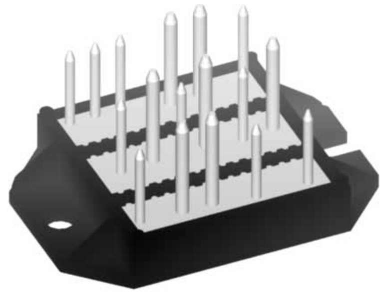
Six-Pack
XPT IGBT

V_{CES} = 1200 V
I_{C25} = 28 A
$V_{CE(sat)}$ = 2.1 V

Part name (Marking on product)

MIXA20W1200MC





Features:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
  - short circuit rated for 10 µsec.
  - very low gate charge
  - square RBSOA @ 3x I_C
  - low EMI
- Thin wafer technology combined with the XPT design results in a competitive low $V_{CE(sat)}$
- SONIC™ diode
  - fast and soft reverse recovery
  - low operating forward voltage

Application:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies

Package:

- "ECO-PAC2" standard package
- Easy to mount with two screws
- Insulated base plate
- Soldering pins for PCB mounting
- Space and weight savings
- Improved temperature and power cycling capability
- High power density

IXYS reserves the right to change limits, test conditions and dimensions.

20110304b

Ouput Inverter T1 - T6

Symbol	Definitions	Conditions		min.	typ.	max.	Unit
					Ratings		
V_{CES}	*collector emitter voltage*		T_{VJ} = 25°C			1200	V
V_{GES} V_{GEM}	*max. DC gate voltage* *max. transient collector gate voltage*	continuous transient				±20 ±30	V V
I_{C25} I_{C80}	*collector current*		T_C = 25°C T_C = 80°C			28 20	A A
P_{tot}	*total power dissipation*		T_C = 25°C			100	W
$V_{CE(sat)}$	*collector emitter saturation voltage*	I_C = 16 A; V_{GE} = 15 V	T_{VJ} = 25°C T_{VJ} = 125°C		1.8 2.1	2.1	V V
$V_{GE(th)}$	*gate emitter threshold voltage*	I_C = 0.6 mA; V_{GE} = V_{CE}	T_{VJ} = 25°C	5.5	6.0	6.5	V
I_{CES}	*collector emitter leakage current*	V_{CE} = V_{CES}; V_{GE} = 0 V	T_{VJ} = 25°C T_{VJ} = 125°C		0.02 0.2	0.2	mA mA
I_{GES}	*gate emitter leakage current*	V_{GE} = ±20 V				500	nA
$Q_{G(on)}$	*total gate charge*	V_{CE} = 600 V; V_{GE} = 15 V; I_C = 15 A			47		nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	*turn-on delay time* *current rise time* *turn-off delay time* *current fall time* *turn-on energy per pulse* *turn-off energy per pulse*	inductive load V_{CE} = 600 V; I_C = 15 A V_{GE} = ±15 V; R_G = 56 Ω	T_{VJ} = 125°C		70 40 250 100 1.55 1.7		ns ns ns ns mJ mJ
RBSOA	*reverse bias safe operating area*	V_{GE} = ±15 V; R_G = 56 Ω;	T_{VJ} = 125°C V_{CEK} = 1200 V			45	A
SCSOA t_{SC} I_{SC}	*short circuit safe operating area* *short circuit duration* *short circuit current*	V_{CE} = 900 V; V_{GE} = ±15 V; R_G = 56 Ω; non-repetitive	T_{VJ} = 125°C		 60	10	µs A
R_{thJC}	*thermal resistance junction to case*	(per IGBT)				1.3	K/W

Output Inverter D1 - D6

Symbol	Definitions	Conditions		min.	typ.	max.	Unit
					Ratings		
V_{RRM}	*max. repetitve reverse voltage*		T_{VJ} = 25°C			1200	V
I_{F25} I_{F80}	*forward current*		T_C = 25°C T_C = 80°C			33 22	A A
V_F	*forward voltage*	I_F = 20 A; V_{GE} = 0 V	T_{VJ} = 25°C T_{VJ} = 150°C		1.95 1.85	2.2	V V
Q_{rr} I_{RM} t_{rr} E_{rec}	*reverse recovery charge* *max. reverse recovery current* *reverse recovery time* *reverse recovery energy*	V_R = 600 V di_F/dt = -400 A/µs I_F = 20 A; V_{GE} = 0 V	T_{VJ} = 125°C		3 20 350 0.7		µC A ns mJ
R_{thJC}	*thermal resistance junction to case*	(per diode)				1.5	K/W

T_C = 25°C unless otherwise stated

Module

Symbol	Definitions	Conditions	min.	typ.	max.	Unit
T_{VJ}	*operating temperature*		-40		125	°C
T_{VJM}	*max. virtual junction temperature*				150	°C
T_{stg}	*storage temperature*		-40		125	°C
V_{ISOL}	*isolation voltage*	$I_{ISOL} \le 1$ mA; 50/60 Hz; t = 1 s			3600	V~
M_d	*mounting torque (M5)*		1.5		2	Nm
d_S	*creep distance on surface*		11.2			mm
d_A	*strike distance through air*		11.2			mm
Weight				24		g

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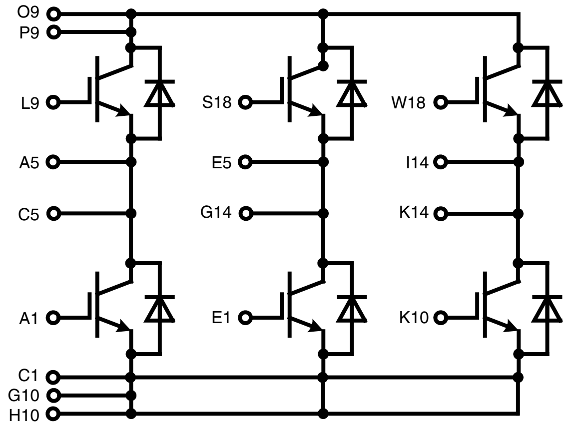
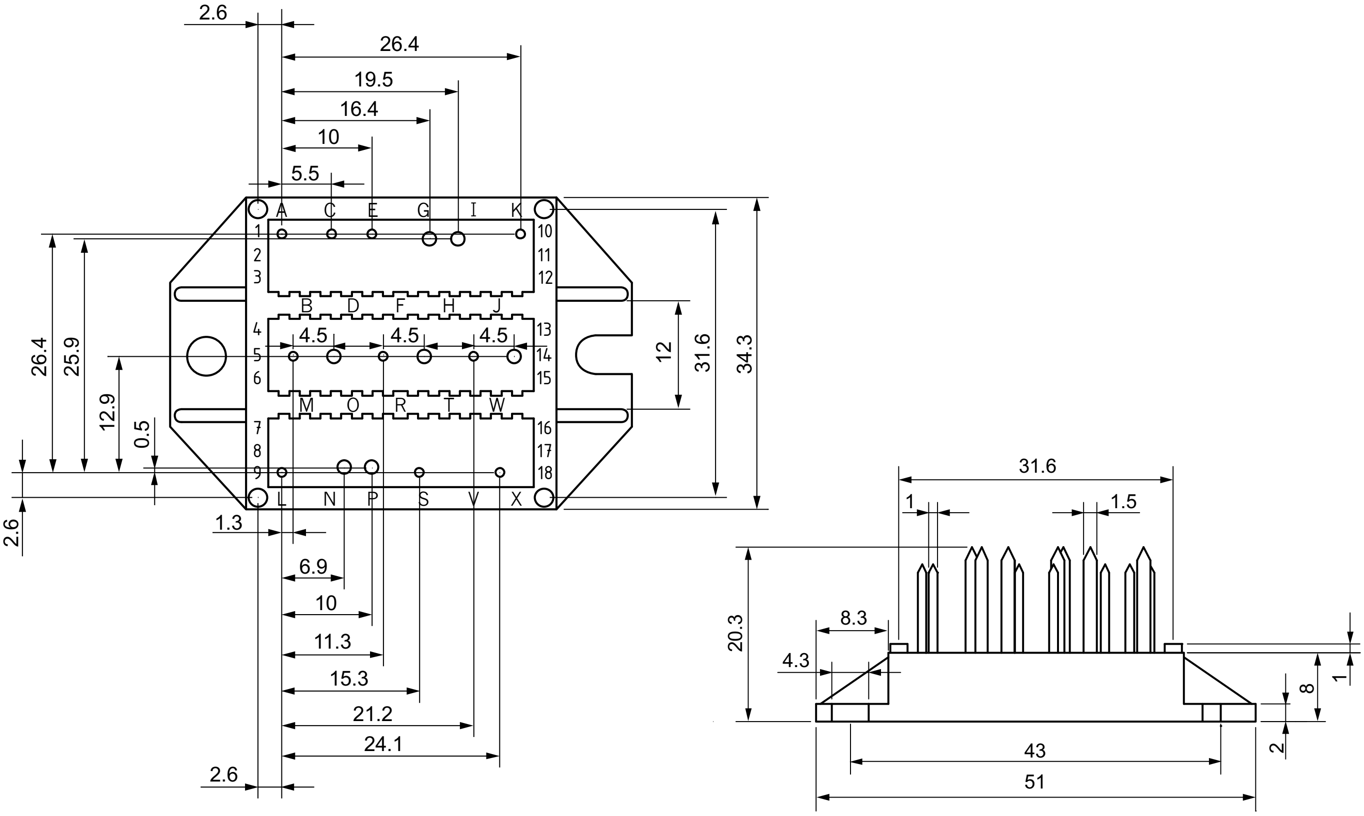
Circuit Diagram

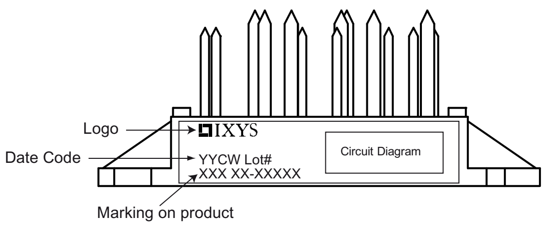


Outline Drawing

Dimensions in mm (1 mm = 0.0394“)



Product Marking



Part number

M = Module
I = IGBT
X = XPT
A = Standard
20 = Current Rating [A]
W = Six-Pack
1200 = Reverse Voltage [V]
MC = ECO-PAC2

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MIXA20W1200MC	MIXA20W1200MC	Box	6	509537

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Inverter T1 - T6

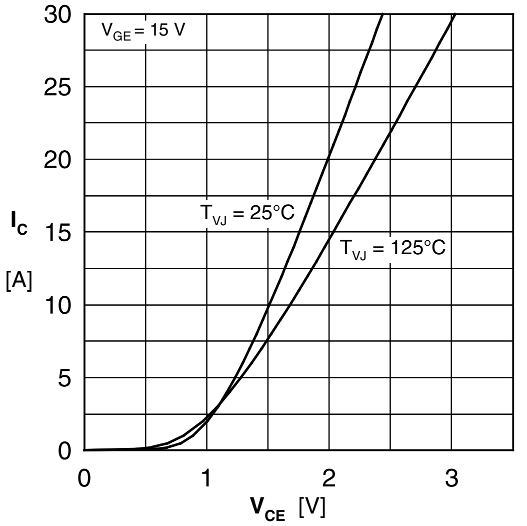

Fig. 1 Typ. output characteristics

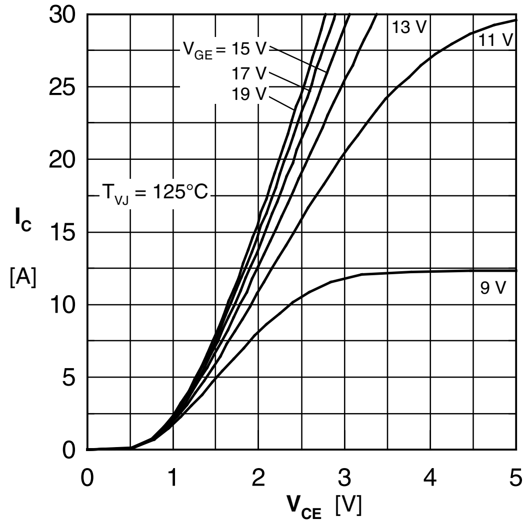

Fig. 2 Typ. output characteristics

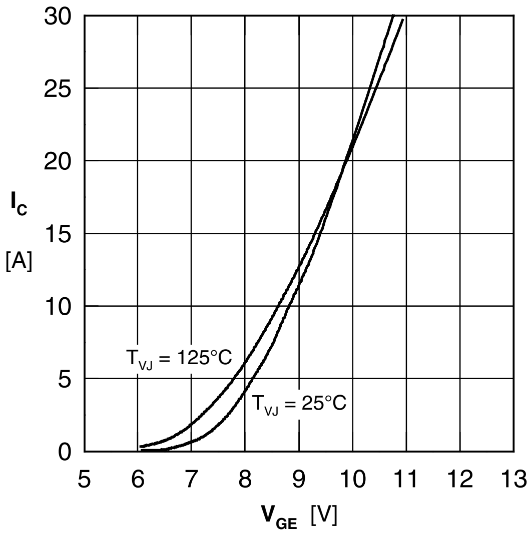

Fig. 3 Typ. tranfer characteristics

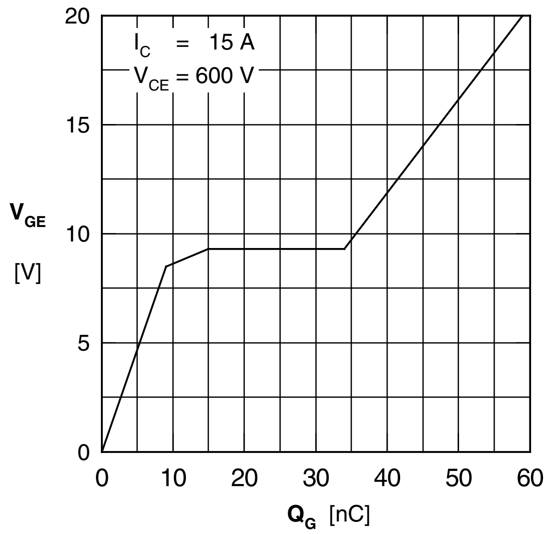

Fig. 4 Typ. turn-on gate charge

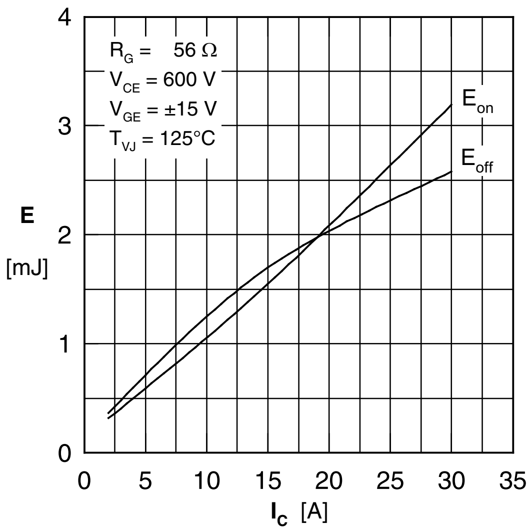

Fig. 5 Typ. switching energy vs. collector current

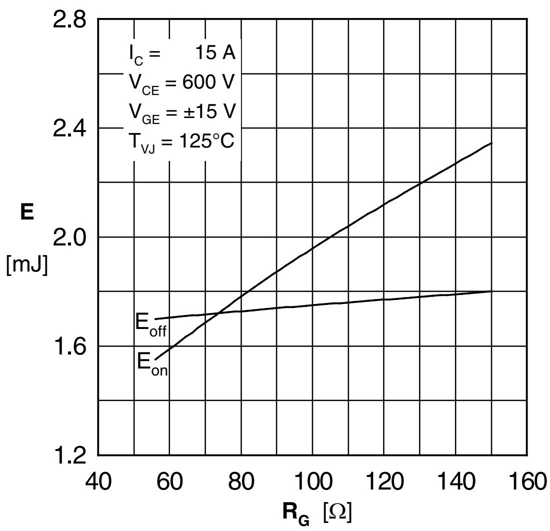

Fig. 6 Typ. switching energy vs. gate resistance

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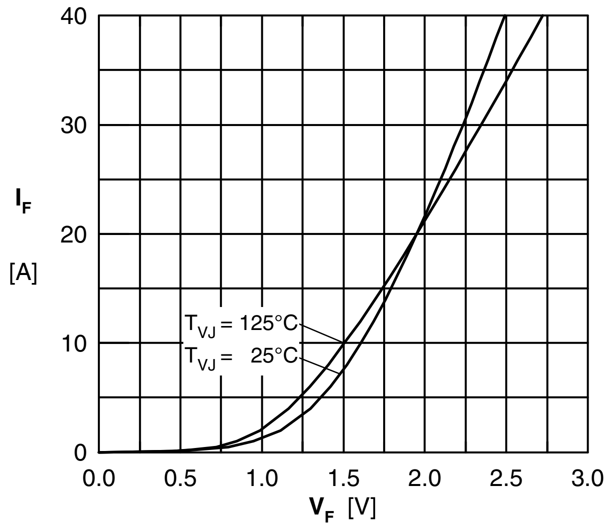

Fig. 7 Typ. Forward current versus V_F

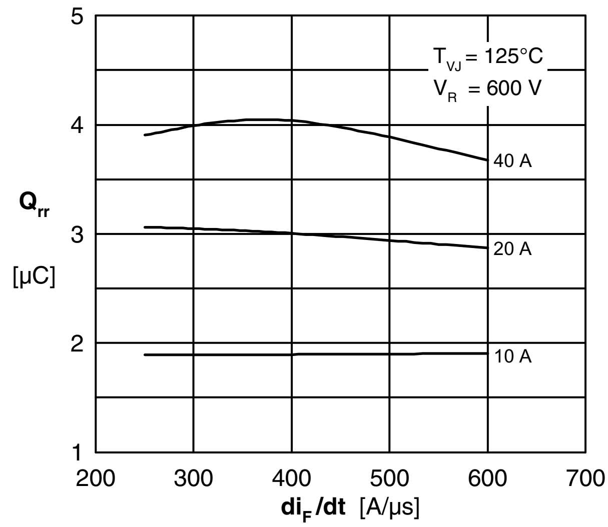

Fig. 8 Typ. reverse recov.charge Q_{rr} vs. di/dt

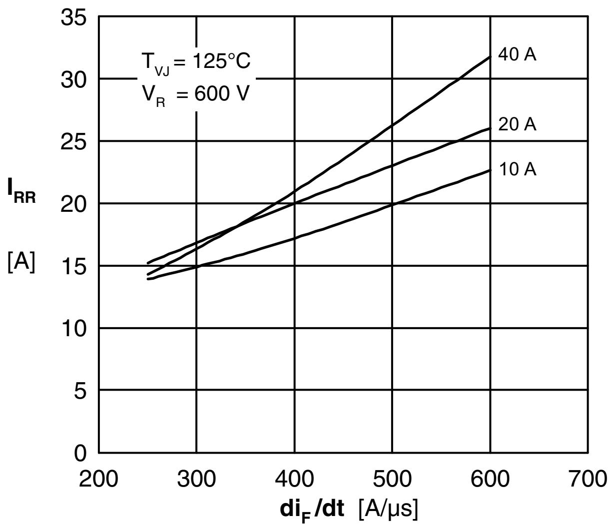

Fig. 9 Typ. peak reverse current I_{RM} vs. di/dt

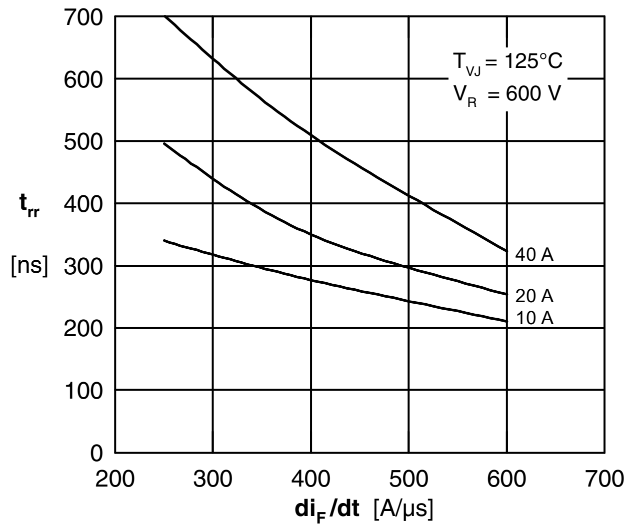

Fig. 10 Typ. recovery time t_{rr} versus di/dt

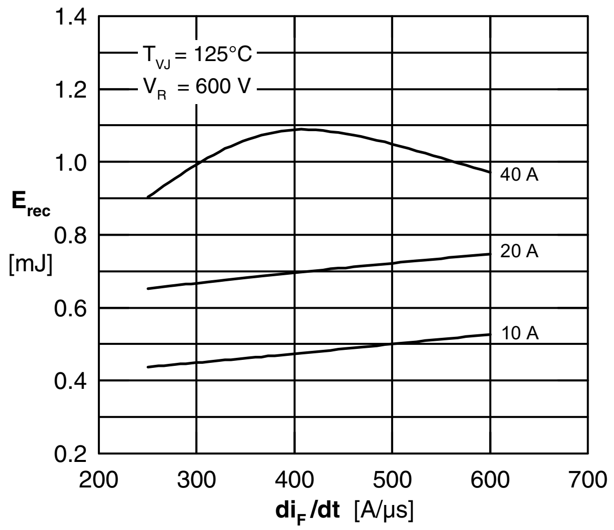

Fig. 11 Typ. recovery energy E_{rec} versus di/dt

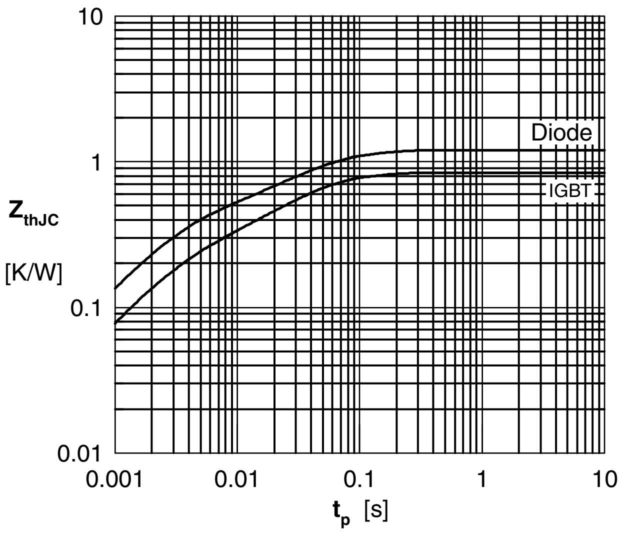

Fig. 12 Typ. transient thermal impedance

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